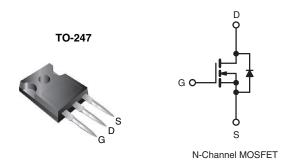
Vishay Siliconix

## **Power MOSFET**



PRODUCT SUMMARY			
V <sub>DS</sub> (V) 500			
$R_{DS(on)}(\Omega)$	V <sub>GS</sub> = 10 V 0.27		
Q <sub>g</sub> (max.) (nC)	120		
Q <sub>gs</sub> (nC)	32		
Q <sub>gd</sub> (nC)	49		
Configuration	Single		

### **FEATURES**

- Ultra low gate charge
- Reduced gate drive requirement
- Enhanced 30 V V<sub>GS</sub> rating
- Reduced Ciss, Coss, Crss
- Isolated central mounting hole
- Dynamic dV/dt rating
- · Repetitive avalanche rated
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### **DESCRIPTION**

This new series of low charge Power MOSFETs achieve significantly lower gate charge over conventional MOSFETs. Utilizing advanced Power MOSFETs technology the device improvements allow for reduced gate drive requirements, faster switching speeds and increased total system savings. These device improvements combined with the proven ruggedness and reliability of Power MOSFETs offer the designer a new standard in power transistors for switching applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole.

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP460LCPbF

ABSOLUTE MAXIMUM RATINGS T <sub>C</sub>	= 25 °C, unle	ess otherwis	e noted		
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			$V_{DS}$	500	V
Gate-source voltage			$V_{GS}$	± 30	V
Continuous drain current	V <sub>GS</sub> at 10 V	$T_{\rm C} = 25  ^{\circ}{\rm C}$ $T_{\rm C} = 100  ^{\circ}{\rm C}$	I_	20	
Continuous drain current	VGS at 10 V	T <sub>C</sub> = 100 °C	I <sub>D</sub>	12	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	80	
Linear derating Factor				2.2	W/°C
Single pulse avalanche energy b			E <sub>AS</sub>	960	mJ
Repetitive avalanche current <sup>a</sup>			I <sub>AR</sub>	20	Α
Repetitive avalanche energy <sup>a</sup>			E <sub>AR</sub>	28	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C		$P_{D}$	280	W
Peak diode recovery dV/dtc			dV/dt	3.5	V/ns
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stq</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) for 10 s				300 d	7
Mauratina taurus		orou		10	lbf ⋅ in
Mounting torque	0-32 OF IVIS	6-32 or M3 screw		1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b.  $V_{DD}$  = 25 V, starting  $T_J$  = 25 °C, L = 4.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AS}$  = 20 A (see fig. 12)
- c.  $I_{SD} \le 20$  A,  $dI/dt \le 160$  A/µs,  $V_{DD} \le V_{DS}$ ,  $T_J \le 150$  °C
- d. 1.6 mm from case

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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	=	
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum junction-to-case (Drain)	R <sub>thJC</sub>	-	0.45	

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 2$	250 μA	500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	°C, I <sub>D</sub> = 1 mA	-	0.59	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 2$	250 μΑ	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 500 \text{ V}, V_{GS}$ $V_{DS} = 400 \text{ V}, V_{GS}$	<sub>S</sub> = 0 V <sub>S</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	25 250	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A <sup>b</sup>	-	-	0.27	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D} =$	12 A <sup>b</sup>	12	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V,		-	3600	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V},$		-	440	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1.0 MHz, see	e fig. 5	-	39	-	
Total gate charge	Qg	$V_{GS} = 10 \text{ V}$ $I_D = 20 \text{ A}, V_{DS} = 400 \text{ V},$ see fig. 6 and 13 b		-	-	120	nC
Gate-source charge	Q <sub>gs</sub>			-	-	32	
Gate-drain charge	Q <sub>gd</sub>			-	-	49	
Turn-on delay time	t <sub>d(on)</sub>	$V_{DD}$ = 250 V, $I_{D}$ = 20 A $R_{G}$ = 4.3 Ω, $R_{D}$ = 12 Ω, see fig. 10 b		-	18	-	ns
Rise time	t <sub>r</sub>			-	77	-	
Turn-off delay time	t <sub>d(off)</sub>			-	40	-	
Fall time	t <sub>f</sub>		1		43	-	
Internal drain inductance	L <sub>D</sub>	Between lead,	ر - ک	-	5.0	-	
Internal source inductance	L <sub>S</sub>	6 mm (0.25") from package and center of die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	cs						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>			-	-	80	А
Body diode voltage	$V_{SD}$	$T_{J} = 25  ^{\circ}\text{C},  I_{S} = 25  ^{\circ}$	20 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.8	V
Body diode reverse recovery time	t <sub>rr</sub>	T 05 °C 1 '	00 A 41/4+ 100 A/: h	-	570	860	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C}, I_F = 20  \text{A}, dI/dt = 100  \text{A/} \mu \text{s}^{ \text{b}}$		-	6.6	9.9	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_T$					

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300 \ \mu s$ ; duty cycle  $\leq 2 \ \%$



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

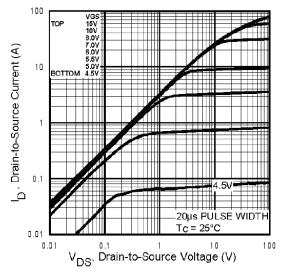


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

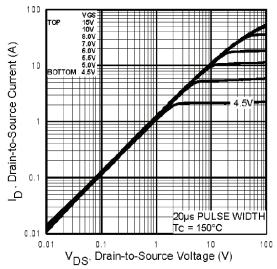


Fig. 2 - Typical Output Characteristics,  $T_C = 150$  °C

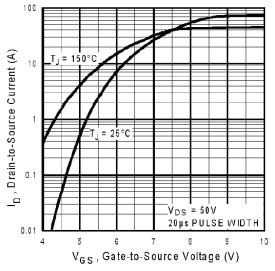


Fig. 3 - Typical Transfer Characteristics

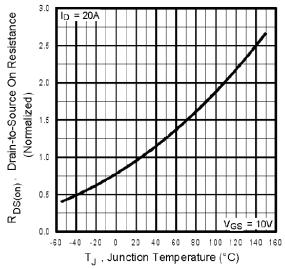


Fig. 4 - Normalized On-Resistance vs. Temperature



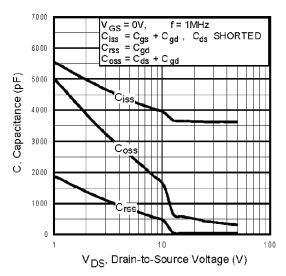


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

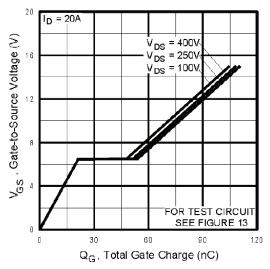


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

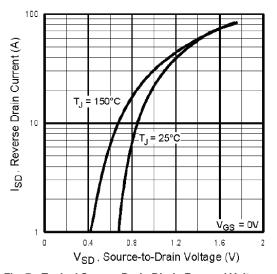


Fig. 7 - Typical Source-Drain Diode Forward Voltage

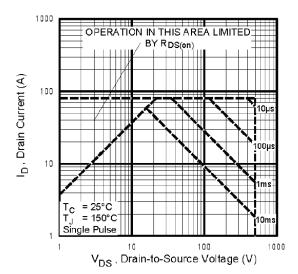


Fig. 8 - Maximum Safe Operating Area



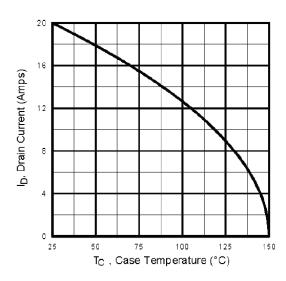


Fig. 9 - Maximum Drain Current vs. Case Temperature

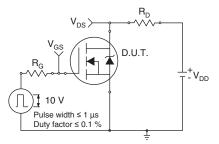


Fig. 10 - Switching Time Test Circuit

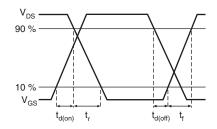


Fig. 11 - Switching Time Waveforms

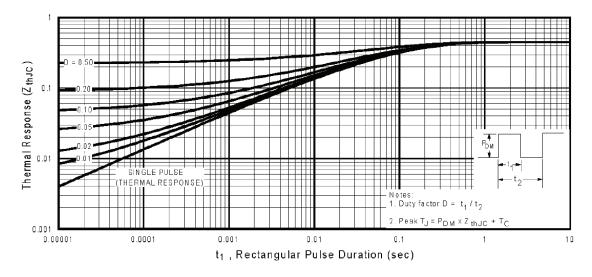


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



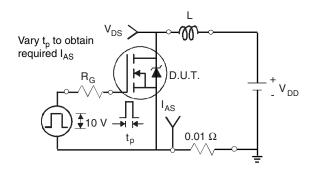


Fig. 13 - Unclamped Inductive Test Circuit

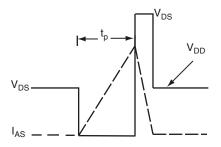


Fig. 14 - Unclamped Inductive Waveforms

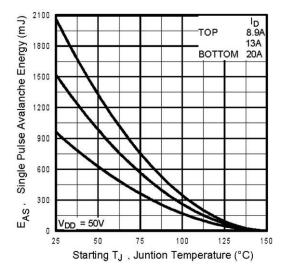


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

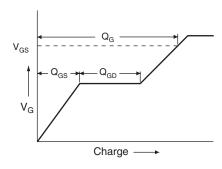


Fig. 16 - Basic Gate Charge Waveform

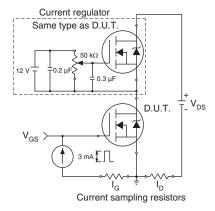
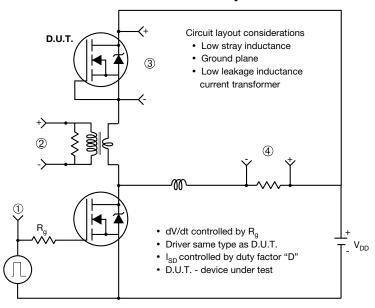


Fig. 17 - Gate Charge Test Circuit



### Peak Diode Recovery dV/dt Test Circuit



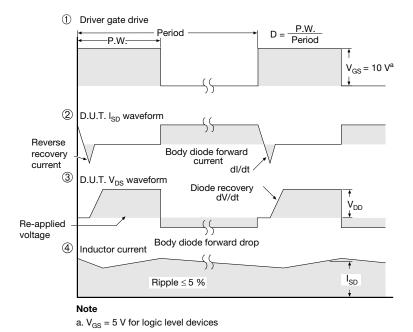


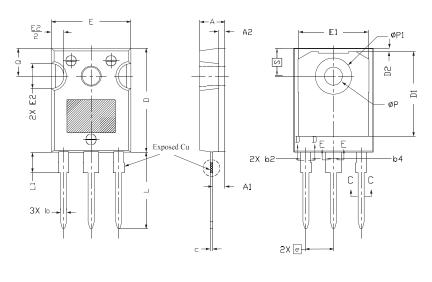
Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?91235">www.vishay.com/ppg?91235</a>.



# **TO-247AC (High Voltage)**

### **VERSION 1: FACILITY CODE = 9**







Section C--C,D-D,E-E

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.17	1.27	1.37		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39	6	
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22	6, 8	
b5	2.87	3.00	3.18		
С	0.40	0.50	0.60	6	
c1	0.40	0.50	0.56		
D	20.40	20.55	20.70	4	

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

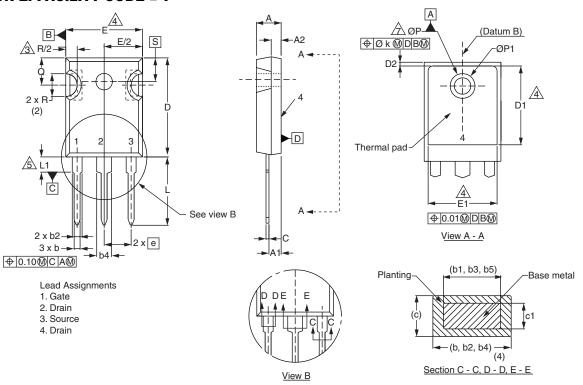
- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$  Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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### **VERSION 2: FACILITY CODE = Y**



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

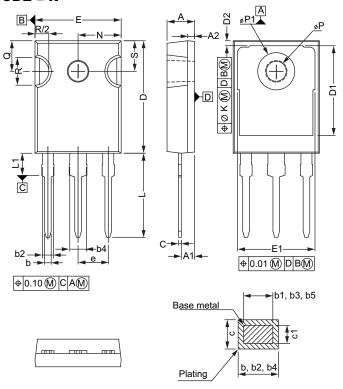
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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### **VERSION 3: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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